

# **BZV55** series

# Voltage regulator diodes

Rev. 5 — 26 January 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Low-power voltage regulator diodes in small hermetically sealed glass SOD80C Surface-Mounted Device (SMD) packages. The diodes are available in the normalized E24  $\pm 2$  % (BZV55-B) and approximately  $\pm 5$  % (BZV55-C) tolerance range. The series consists of 37 types with nominal working voltages from 2.4 V to 75 V.

#### 1.2 Features and benefits

- Non-repetitive peak reverse power dissipation: ≤ 40 W
- Total power dissipation: ≤ 500 mW
- Two tolerance series: ±2 % and ±5 %
- Wide working voltage range: nominal 2.4 V to 75 V (E24 range)
- Low differential resistance
- Small hermetically sealed glass
   SMD package

#### 1.3 Applications

General regulation functions

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage	$I_F = 10 \text{ mA}$	-	-	0.9	V
P <sub>ZSM</sub>	non-repetitive peak reverse power dissipation		[1] _	-	40	W

<sup>[1]</sup>  $t_p = 100 \mu s$ ; square wave;  $T_j = 25 \,^{\circ}C$  prior to surge

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	
2	anode	k	1 2 006aaa152

<sup>[1]</sup> The marking band indicates the cathode.



## 3. Ordering information

Table 3. Ordering information

Type number	Package	Package							
	Name	Description	Version						
BZV55-B2V4 to BZV55-C75[1]	-	hermetically sealed glass surface-mounted package; 2 connectors	SOD80C						

<sup>[1]</sup> The series consists of 74 types with nominal working voltages from 2.4 V to 75 V.

## 4. Marking

Table 4. Marking codes

Type number	Marking code
BZV55-B2V4 to BZV55-C75	marking band

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>F</sub>	forward current		-	250	mA
I <sub>ZSM</sub>	non-repetitive peak reverse current		<u>[1]</u> -	see Table 8 and 9	
P <sub>ZSM</sub>	non-repetitive peak reverse power dissipation		[1] _	40	W
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 50 °C	[2] _	400	mW
		$T_{tp} \le 50  ^{\circ}C$	[2] _	500	mW
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature		-65	+200	°C

<sup>[1]</sup>  $t_p = 100 \mu s$ ; square wave;  $T_j = 25 \,^{\circ}C$  prior to surge

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	380	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	300	K/W

<sup>[1]</sup> Device mounted on a ceramic substrate of  $10 \times 10 \times 0.6$  mm.

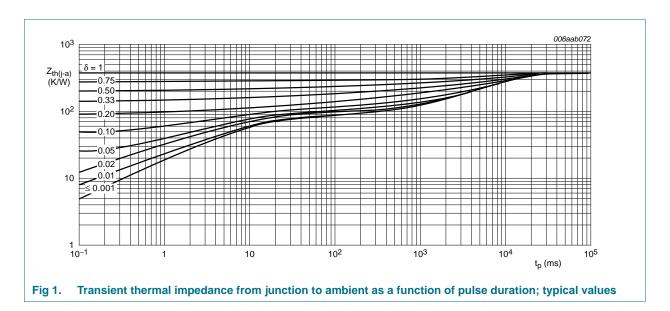
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**Product data sheet** 

<sup>[2]</sup> Device mounted on a ceramic substrate of  $10 \times 10 \times 0.6$  mm.



### 7. Characteristics

**Table 7.** Characteristics  $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	$I_F = 10 \text{ mA}$	-	-	0.9	V
l <sub>R</sub>	reverse current					
	BZV55-B/C2V4	V <sub>R</sub> = 1 V	-	-	50	μΑ
	BZV55-B/C2V7	$V_R = 1 V$	-	-	20	μΑ
	BZV55-B/C3V0	$V_R = 1 V$	-	-	10	μΑ
	BZV55-B/C3V3	V <sub>R</sub> = 1 V	-	-	5	μΑ
	BZV55-B/C3V6	$V_R = 1 V$	-	-	5	μΑ
	BZV55-B/C3V9	V <sub>R</sub> = 1 V	-	-	3	μΑ
	BZV55-B/C4V3	$V_R = 1 V$	-	-	3	μΑ
	BZV55-B/C4V7	$V_R = 2 V$	-	-	3	μΑ
	BZV55-B/C5V1	$V_R = 2 V$	-	-	2	μΑ
	BZV55-B/C5V6	$V_R = 2 V$	-	-	1	μΑ
	BZV55-B/C6V2	$V_R = 4 V$	-	-	3	μΑ
	BZV55-B/C6V8	$V_R = 4 V$	-	-	2	μΑ
	BZV55-B/C7V5	$V_R = 5 V$	-	-	1	μΑ
	BZV55-B/C8V2	$V_R = 5 V$	-	-	700	nΑ
	BZV55-B/C9V1	V <sub>R</sub> = 6 V	-	-	500	nΑ
	BZV55-B/C10	$V_R = 7 V$	-	-	200	nΑ
	BZV55-B/C11	V <sub>R</sub> = 8 V	-	-	100	nA
	BZV55-B/C12	V <sub>R</sub> = 8 V	-	-	100	nA
	BZV55-B/C13	V <sub>R</sub> = 8 V	-	-	100	nA
	BZV55-B/C15 to BZV55-B/C75	$V_R = 0.7V_{Z(nom)}$	_	-	50	nA

BZV55\_SER

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Table 8. Characteristics per type; BZV55-B2V4 to BZV55-C24

 $T_i = 25$  °C unless otherwise specified.

BZV55- xxx	Sel	Worki voltag V <sub>Z</sub> (V)	je	Differ	rential ro 2)	esistar	nce	Temp coeffi S <sub>Z</sub> (m			Diode capacitance C <sub>d</sub> (pF)[1]	Non-repetitive peak reverse current
		I <sub>Z</sub> = 5	mA	I <sub>Z</sub> = 1	mA	I <sub>Z</sub> = 5	mA	I <sub>Z</sub> = 5	mA			I <sub>ZSM</sub> (A)[2]
		Min	Max	Тур	Max	Тур	Max	Min	Тур	Max	Max	Max
2V4	В	2.35	2.45	275	600	70	100	-3.5	-1.6	0	450	6.0
	С	2.2	2.6									
2V7	2V7 B 2.65 2.75	2.75	300	600	75	100	-3.5	-2.0	0	450	6.0	
	С	2.5	2.9									
3V0	В	2.94	3.06	325	600	80	95	-3.5	-2.1	0	450	6.0
	С	2.8	3.2									
3V3	В	3.23	3.37	350	600	85	95	-3.5	-2.4	0	450	6.0
	С	3.1	3.5									
3V6	В	3.53	3.67	375	600	85	90	-3.5	-2.4	0	450	6.0
	С	3.4	3.8									
3V9	В	3.82	3.98	400	600	85	90	-3.5	-2.5	0	450	6.0
	С	3.7	4.1									
4V3	В	4.21	4.39	410	600	80	90	-3.5	-2.5	2.5 0	450	6.0
	С	4.0	4.6									
4V7	В	4.61	4.79	425	500	50	80	-3.5	-1.4	0.2	300	6.0
	С	4.4	5.0									
5V1	В	5.0	5.2	400	480	40	60	-2.7	-0.8	1.2	300	6.0
	С	4.8	5.4									
5V6	В	5.49	5.71	80	400	15	15 40	-2.0	-2.0 1.2	2.5	300	6.0
	С	5.2	6.0									
6V2	В	6.08	6.32	40	150	6	10	0.4	2.3	2.3 3.7	200	6.0
	С	5.8	6.6									
6V8	В	6.66	6.94	30	80	6	15	1.2	3.0	4.5	200	6.0
	С	6.4	7.2									
7V5	В	7.35	7.65	30	80	6	15	2.5	4.0	5.3	150	4.0
	С	7.0	7.9									
8V2	В	8.04	8.36	40	80	6	15	3.2	4.6	6.2	150	4.0
	С	7.7	8.7									
9V1	В	8.92	9.28	40	100	6	15	3.8	5.5	7.0	150	3.0
	С	8.5	9.6									
10	В	9.8	10.2	50	150	8	20	4.5	6.4	8.0	90	3.0
	С	9.4	10.6									
11	В	10.8	11.2	50	150	10	20	5.4	7.4	9.0	85	2.5
	С	10.4	1 11.6									
12	В	11.8	12.2	50	150	10	25	6.0	8.4	10.0	85	2.5
	С	11.4	12.7									

BZV55\_SEF

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Table 8. Characteristics per type; BZV55-B2V4 to BZV55-C24 ...continued

 $T_i = 25$  °C unless otherwise specified.

BZV55- xxx	Sel	Working voltage V <sub>Z</sub> (V)			Differential resistance $r_{dif}(\Omega)$			Tempo coeffi S <sub>Z</sub> (m			Diode capacitance C <sub>d</sub> (pF)[1]	Non-repetitive peak reverse current
		$I_Z = 5 \text{ mA}$		I <sub>Z</sub> = 1	$I_Z = 1 \text{ mA}$ $I_Z = 5 \text{ r}$		$mA$ $I_Z = 5 mA$					I <sub>ZSM</sub> (A)[2]
		Min	Max	Тур	Max	Тур	Max	Min	Тур	Max	Max	Max
13	В	12.7	13.3	50	170	10	30	7.0	9.4	11.0	80	2.5
	С	12.4	14.1									
	В	14.7	15.3	50	200	10	30	9.2	11.4	13.0	75	2.0
	С	13.8	15.6									
16	В	15.7	16.3	50	200	10	10 40	10.4	12.4	14.0	75	1.5
	С	15.3	17.1									
18	В	17.6	18.4	50	50 225	225 10	45	12.4	14.4	16.0	70	1.5
	С	16.8	19.1									
20	В	19.6	20.4	60	225	15	55	12.3	15.6	18.0	60	1.5
	С	18.8	21.2									
22	В	21.6	22.4	60	250	20	55	14.1	17.6	20.0	60	1.25
	С	20.8	23.3									
24	В	23.5	24.5	60	250	) 25	70	15.9	15.9 19.6	19.6 22.0	55	1.25
	С	22.8	25.6									

<sup>[1]</sup>  $f = 1 \text{ MHz}; V_R = 0 \text{ V}$ 

<sup>[2]</sup>  $t_p = 100 \mu s$ ; square wave;  $T_i = 25 \, ^{\circ}C$  prior to surge

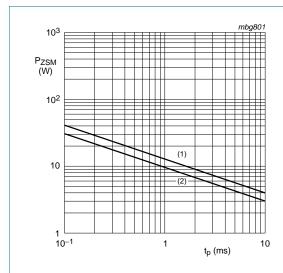
Table 9. Characteristics per type; BZV55-B27 to BZV55-C75

 $T_i = 25$  °C unless otherwise specified.

BZV55- xxx	Sel	Working voltage V <sub>Z</sub> (V)		Differ	rential r 2)	esistar	ice	Temperature coefficient S <sub>Z</sub> (mV/K)			Diode capacitance C <sub>d</sub> (pF) <sup>[1]</sup>	Non-repetitive peak reverse current
		I <sub>Z</sub> = 2	mA	I <sub>Z</sub> = 0	$I_Z = 0.5 \text{ mA}$ $I_Z = 2 \text{ mA}$		I <sub>Z</sub> = 2	mA			I <sub>ZSM</sub> (A)[2]	
		Min	Max	Тур	Max	Тур	Max	Min	Тур	Max	Max	Max
27	В	26.5	27.5	65	300	25	5 80	18.0	3.0 22.7	25.3	5.3 50	1.0
	С	25.1	28.9									
30	В	29.4	30.6	70	300	30	80	20.6	25.7	29.4	50	1.0
	С	28.0	32.0									
33	В	32.3	33.7	75	325	35	80	23.3	28.7	33.4	45	0.9
(	С	31.0	35.0									
36	В	35.3	36.7	80	350	35	90	26.0	31.8	31.8 37.4	37.4 45	0.8
(	С	34.0	38.0									
39 B C	В	38.2	39.8	80	350	40	130	28.7	7 34.8	34.8 41.2	2 45	0.7
	С	37.0	41.0									
43	В	42.1	43.9	85	85 375	375 45	5 150	31.4	38.8	3 46.6	6 40	0.6
	С	40.0	46.0									
47	В	46.1	47.9	85	375	<b>7</b> 5 50	170	0 35.0	5.0 42.9	42.9 51.8	51.8 40	0.5
	С	44.0	50.0									
51	В	50.0	52.0	90	400	60	180	38.6	46.9	57.2	40	0.4
	С	48.0	54.0									
56	В	54.9	57.1	100	425	70	200	42.2	52.0	63.8	40	0.3
	С	52.0	60.0									
62	В	60.8	63.2	120	450	80	215	58.8	64.4	71.6	35	0.3
	С	58.0	66.0									
68	В	66.6	69.4	150	475	90	240	65.6	71.7	79.8	35	0.25
	С	64.0	72.0									
75	В	73.5	76.5	170	500	95	255	5 73.4	73.4 80.2	80.2 88.6	35	0.2
	С	70.0	79.0									

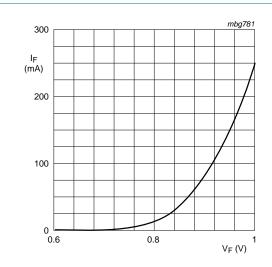
<sup>[1]</sup>  $f = 1 \text{ MHz}; V_R = 0 \text{ V}$ 

<sup>[2]</sup>  $t_p = 100 \mu s$ ; square wave;  $T_j = 25 \, ^{\circ}C$  prior to surge



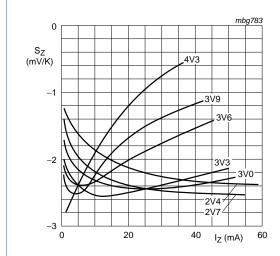
- (1)  $T_j = 25 \,^{\circ}\text{C}$  (prior to surge)
- (2)  $T_i = 150 \,^{\circ}\text{C}$  (prior to surge)

Fig 2. Non-repetitive peak reverse power dissipation as a function of pulse duration; maximum values



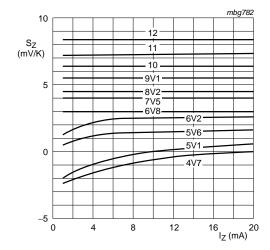
T<sub>j</sub> = 25 °C

Fig 3. Forward current as a function of forward voltage; typical values



BZV55-B/C2V4 to BZV55-B/C4V3  $T_i = 25$  °C to 150 °C

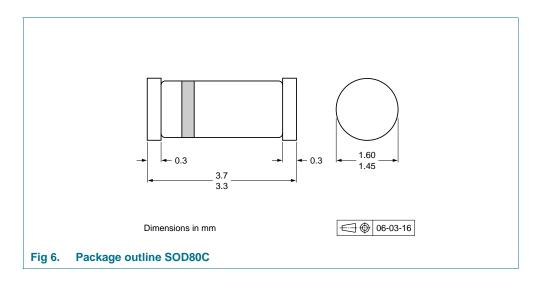
Fig 4. Temperature coefficient as a function of working current; typical values



BZV55-B/C4V7 to BZV55-B/C12  $T_i = 25$  °C to 150 °C

Fig 5. Temperature coefficient as a function of working current; typical values

## 8. Package outline



## 9. Packing information

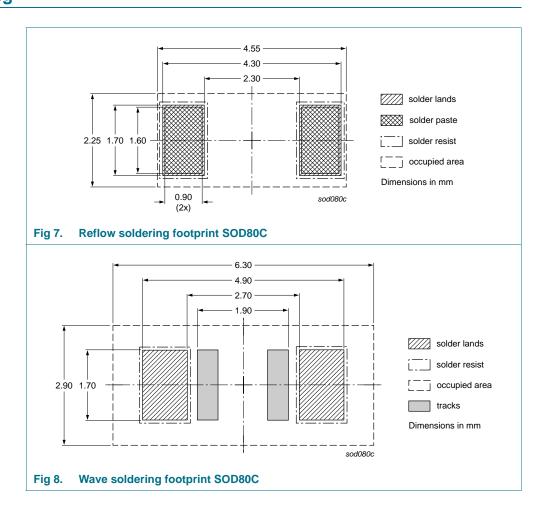
Table 10. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing q	Packing quantity		
			2500	10000		
BZV55-B2V4 to BZV55-C75	SOD80C	4 mm pitch, 8 mm tape and reel	-115	-135		

[1] For further information and the availability of packing methods, see <u>Section 13</u>.

## 10. Soldering



## 11. Revision history

Table 11. Revision history

	•								
Document ID	Release date	Data sheet status	Change notice	Supersedes					
BZV55_SER v.5	20110126	Product data sheet	-	BZV55_SER v.4					
Modifications:	<ul> <li>Section 4 "Mark</li> </ul>	<u>sing"</u> : updated							
	<ul> <li><u>Table 6 "Thermal characteristics"</u>: changed R<sub>th(j-t)</sub> for R<sub>th(j-sp)</sub></li> </ul>								
	<ul> <li>Figure 6: superseded by minimized outline drawing</li> </ul>								
	<ul> <li>Section 12 "Leg</li> </ul>	al information": updated							
BZV55_SER v.4	20070719	Product data sheet	CPCN200508022F	BZV55 v.3					
BZV55 v.3	20020228	Product specification	-	BZV55 v.2					
BZV55 v.2	19990521	Product specification	-	BZV55 v.1					
BZV55 v.1	19960426	Product specification	-	-					

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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### 14. Contents

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